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What is claimed is:

are almost on one plane.

1. A thin film forming equipment comprising:
2 a substrate;
3 a substrate holding device used to hold said substrate;
4 a device used to provide an atmospheric gas to a surface
5 of said substrate held by said substrate holding device; and
6 whereby an upper face of said substrate held by said substrate
7 holding device and an upper face of said substrate holding device

- 2. The thin film forming equipment according to claim 1, wherein said substrate holding device is provided with a trench along a circumference of said held substrate and said atmospheric gas is able to be discharged through said trench.
- 3. The thin film forming equipment according to claim
 1, wherein a sheet is provided at a boundary between said held
 3 substrate and said substrate holding device.
- The thin film forming equipment according to claim 1 2 1, wherein said thin film forming equipment provides said 3 atmospheric gas to the surface of said subst $oldsymbol{\chi}$ ate held by said 4 substrate holding device and forms said thing film on said substrate by decomposing said atmospheric gas; and wherein: said 5 thin film forming equipment further comprises gas introducing 6 means for introducing said atmospheric gas, a gas retention 7 chamber for retention of said introduced gas using said gas 8 9 introducing means, gas discharging means for discharging gas

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10 ejected from said gas retention means and laser radiating means

11 for decomposing gas staying at said gas retention chamber by

12 laser irradiation.

1 \displays A thin film forming equipment comprising:

2 a substrate;

a substrate holding device used to hold said substrate;

a device used to provide an atmospheric gas to a surface of said substrate held by said substrate holding device;

whereby an upper face of said substrate held by said substrate holding device and an upper face of said substrate holding device are almost on one plane; and

wherein said substrate holding device has a cover body which is disposed in an area surrounding said substrate held by said substrate holding device and wherein an upper face of said cover body and the upper face of said substrate are almost on one plane.

1 6. The thin film forming equipment according to claim
2 5, wherein said substrate holding device is provided with a trench
3 along a circumference of said held substrate and said atmospheric
4 gas is able to be discharged through said trench.

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- 7. The thin film forming equipment according to claim
 5, wherein a sheet is provided at a boundary between said held
 substrate and said substrate holding device.
- 1 8. The thin film forming equipment according to claim
 2 5, wherein said thin film forming equipment provides said

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atmospheric gas to the surface of said substrate held by said 3 substrate holding device and forms said thin film on said 4 substrate by decomposing said atmospheric gas; and wherein: said 5 thin film forming equipment further comprises gas introducing 6 means for introducing said atmospheric gas, a gas retention 7 chamber for retention of said introduced gas using said gas 8 introducing means, gas discharging means for discharging gas 9 ejected from said gas retention means and laser radiating means 10 for decomposing gas staying at said gas retention chamber by laser irradiation.

- 9. A method for forming a thin film on a substrate by decomposing gas introduced to a surface of a substrate held by a substrate holding device comprising a step of preventing said gas introduced to said surface of said substrate from being influenced by outside air.
- 1 10. The method for forming the thin film according to 2 claim 9, wherein an upper face of said substrate and an upper 3 face of said substrate holding device are almost on one plane 4 to prevent gas introduced on said substrate surface from being influenced by outside gas. 5
- 1 11. A method for forming a thin film on a substrate by 2 introducing gas to a surface of a substrate held by a substrate holding device, by radiating said introduced gas with laser, 3 by decomposing said introduced gas and then by suctioning and 4 5 discharging decompositional by-products, comprising a step of 6 preventing said gas introduced to said surface of said substrate

- 7 from being influenced by outside air.
- 1 12. The method for forming the thin film according to
- 2 claim 11, wherein an upper face of said substrate and an upper
- 3 face of said substrate holding device are almost on one plane
- 4 to prevent gas introduced on said substrate surface from being
- 5 influenced by outside gas.